



In the United States Patent and Trademark Office

Inventor: E. Morita)
Serial No.: 09/726,860)
Title: Method of Manufacturing Crystal of III-V...)
Atty. Docket No. 9792909-4715)

Examiner: M. Anderson

Group Unit: 1765

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Response D to Final Office Action dated 04 Feb. 2003

In response to the Final Office Action dated 04 Feb. 2003, the applicant responds as follows.

A. In the Claims

1. (currently amended) A method of manufacturing a crystal of a III-V compound of the nitride system, the method including:

(a) a first growth step to form a first crystal layer, the first crystal layer further having a surface, by growing a crystal of a III-V compound of the nitride system on a surface of a basal body;

(b) a first mask forming step to form a first mask pattern on the surface of the first crystal layer;

(c) a first etching step to etch the first crystal layer through the first mask pattern;

(d) a second growth step to form a second crystal layer, the second crystal layer further having a surface, by growing a crystal of a III-V compound of the nitride system from the first crystal layer;

(e) a second mask forming step to form a second mask pattern on the surface of the second crystal layer and ensuring that the second mask overlies a window in the first mask;

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